www.ti.com

SGLS367C-SEPTEMBER 2006-REVISED MARCH 2007

3.3-V FULL-DUPLEX RS-485 DRIVERS AND RECEIVERS

FEATURES

- Controlled Baseline
 - One Assembly Site
 - One Test Site
 - One Fabrication Site
- Extended Temperature Performance of -55°C to 125°C
- Enhanced Diminishing Manufacturing Sources (DMS) Support
- Enhanced Product-Change Notification
- Qualification Pedigree⁽¹⁾
- Available in the Texas Instruments
 NanoStar[™] and NanoFree[™] Packages
- 1/8 Unit-Load Option Available (up to 256 Nodes on the Bus)
- Bus-Pin ESD Protection Exceeds 15-kV HBM
- Optional Driver Output Transition Times for Signaling Rates⁽²⁾ of 1 Mbps, 5 Mbps, and 25 Mbps
- Low-Current Standby Mode: <1 μA
- Glitch-Free Power-Up and Power-Down Protection for Hot-Plugging Applications
- 5-V-Tolerant Inputs
- Bus Idle, Open, and Short-Circuit Fail Safe
- Driver Current Limiting and Thermal Shutdown
- Meet or Exceed the Requirements of ANSI TIA/EIA-485-A and RS-422 Compatible
- (1) Component qualification in accordance with JEDEC and industry standards to ensure reliable operation over an extended temperature range. This includes, but is not limited to, Highly Accelerated Stress Test (HAST) or biased 85/85, temperature cycle, autoclave or unbiased HAST, electromigration, bond intermetallic life, and mold compound life. Such qualification testing should not be viewed as justifying use of this component beyond specified performance and environmental limits.
- (2) The signaling rate of a line is the number of voltage transitions that are made per second expressed in the units bps (bits per second).

APPLICATIONS

- Utility Meters
- DTE/DCE Interfaces
- Industrial, Process, and Building Automation
- Point-of-Sale (POS) Terminals and Networks

DESCRIPTION

The SN65HVD3x devices are 3-state differential line drivers and differential-input line receivers that operate with 3.3-V power supply.

Each driver and receiver has separate input and output pins for full-duplex bus communication designs. They are designed for balanced transmission lines and interoperation with ANSI TIA/EIA-485A, TIA/EIA-422-B, ITU-T v.11, and ISO 8482:1993 standard-compliant devices.

The SN65HVD30, SN65HVD31, SN65HVD32, SN65HVD36, and SN65HVD37 are fully enabled with no external enabling pins. The SN65HVD36 and SN65HVD37 implement receiver equalization technology for improved performance in long distance applications.

The SN65HVD33, SN65HVD34, SN65HVD35, SN65HVD38, and SN65HVD39 have active-high driver enables and active-low receiver enables. A low (less than 1 μA) standby current can be achieved by disabling both the driver and receiver. The SN65HVD38 and SN65HVD39 implement receiver equalization technology for improved performance in long distance applications.

The SN65HVD36 and SN65HVD38 implement receiver equalization technology for improved jitter performance on differential bus applications with data rates up to 20 Mbps at cable lengths up to 160 meters.

The SN65HVD37 and SN65HVD39 implement receiver equalization technology for improved jitter performance on differential bus applications with data rates in the range of 1 Mbps to 5 Mbps at cable lengths up to 1000 meters.

All devices are characterized for operation from –55°C to 125°C.

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

NanoStar, NanoFree are trademarks of Texas Instruments.

SGLS367C-SEPTEMBER 2006-REVISED MARCH 2007

IMPROVED REPLACEMENT FOR:

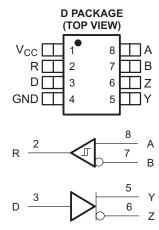
Part Number	Replace With	
xxx3491 xxx3490	SN65HVD33: SN65HVD30:	Better ESD protection (15 kV vs 2 kV or not specified), higher signaling rate (25 Mbps vs 20 Mbps), fractional unit load (64 nodes vs 32)
MAX3491E MAX3490E	SN65HVD33: SN65HVD30:	Higher signaling rate (25 Mbps vs 12 Mbps), fractional unit load (64 nodes vs 32)
MAX3076E MAX3077E	SN65HVD33: SN65HVD30:	Higher signaling rate (25 Mbps vs 16 Mbps), lower standby current (1 μ A vs 10 μ A)
MAX3073E MAX3074E	SN65HVD34: SN65HVD31:	Higher signaling rate (5 Mbps vs 500 kbps), lower standby current (1 μ A vs 10 μ A)
MAX3070E MAX3071E	SN65HVD35: SN65HVD32:	Higher signaling rate (1 Mbps vs 250 kbps), lower standby current (1 μ A vs 10 μ A)



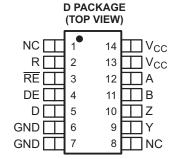
This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

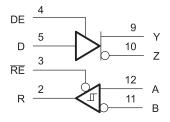
SN65HVD30, SN65HVD31, SN65HVD32, SN65HVD36, SN65HVD37



SN65HVD33, SN65HVD34, SN65HVD35, SN65HVD38, SN65HVD39



NC - No internal connection







SGLS367C-SEPTEMBER 2006-REVISED MARCH 2007

AVAILABLE OPTIONS(1)

BASE PART NUMBER	SIGNALING RATE	UNIT LOADS	RECEIVER EQUALIZATION	ENABLES	SOIC MARKING
SN65HVD30MDREP	25 Mbps		No	No	HVD30EP
SN65HVD31MDREP (2)	5 Mbps	1/8	No	No	PREVIEW
SN65HVD32MDREP ⁽²⁾	1 Mbps	1/8	No	No	PREVIEW
SN65HVD33MDREP	25 Mbps		No	Yes	HVD33EP
SN65HVD34MDREP ⁽²⁾	5 Mbps	1/8	No	Yes	PREVIEW
SN65HVD35MDREP ⁽²⁾	1 Mbps	1/8	No	Yes	PREVIEW
SN65HVD36MDREP ⁽²⁾	25 Mbps		Yes	No	PREVIEW
SN65HVD37MDREP ⁽²⁾	5 Mbps	1/8	Yes	No	PREVIEW
SN65HVD38MDREP ⁽²⁾	25 Mbps		Yes	Yes	PREVIEW
SN65HVD39MDREP ⁽²⁾	5 Mbps	1/8	Yes	Yes	PREVIEW

⁽¹⁾ For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI Web site at www.ti.com.

Absolute Maximum Ratings (1)(2)

over operating free-air temperature range (unless otherwise noted)

		UNIT
V _{CC}	Supply voltage range	–0.3 V to 6 V
V _(A) , V _(B) , V _(Y) , V _(Z)	Voltage range at any bus terminal (A, B, Y, Z)	–9 V to 14 V
V _(TRANS)	Voltage input, transient pulse through 100 Ω (see Figure 12) (A, B, Y, Z) ⁽³⁾	–50 V to 50 V
V _I	Input voltage range (D, DE, RE)	–0.5 V to 7 V
P _{D(cont)}	Continuous total power dissipation	Internally limited ⁽⁴⁾
Io	Output current (receiver output only, R)	11 mA
T _J	Junction temperature	165°C
T _{STG}	Storage temperature range	-65°C to 150°C

⁽¹⁾ Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

⁽²⁾ Product Preview

⁽²⁾ All voltage values, except differential I/O bus voltages, are with respect to network ground terminal.

⁽³⁾ This tests survivability only and the output state of the receiver is not specified.

⁽⁴⁾ The thermal shutdown protection circuit internally limits the continuous total power dissipation. Thermal shutdown typically occurs when the junction temperature reaches 165°C.

SN65HVD30-EP, SN65HVD31-EP, SN65HVD32-EP, SN65HVD33-EP, SN65HVD34-EP SN65HVD35-EP, SN65HVD36-EP, SN65HVD37-EP, SN65HVD38-EP, SN65HVD39-EP



SGLS367C-SEPTEMBER 2006-REVISED MARCH 2007

Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

					MIN	NOM	MAX	UNIT
V _{CC}	Supply voltage				3		3.6	V
V _I or V _{IC}	Voltage at any bus	s terminal (ser	eparate	ly or common mode)	-7 ⁽¹⁾		12	V
	'HVD30, 'HVD33, 'HVD36, 'HVD38		'HVD36, 'HVD38			25		
1/t _{UI}	Signaling rate	'HVD31, 'H\	VD34,	'HVD37, 'HVD39			5	Mbps
		'HVD32, 'H\	VD35				1	
R_L	Differential load re	sistance			54	60		Ω
V _{IH}	High-level input vo	oltage	D, E	DE, RE	2		V_{CC}	V
V_{IL}	Low-level input vo	ltage	D, E	DE, RE	0		0.8	V
V_{ID}	Differential input v	oltage			-12		12	V
	I limb lavel avitovit a		Driv	ver	-60			A
ІОН	High-level output current		Rec	ceiver	-8			mA
I _{OL} Low-level output curren			Driv	ver			60	1
		urrent	Rec	ceiver			8	mA
T _A	Ambient still-air te	mperature	•		-55		125 ⁽²⁾	°C

⁽¹⁾ The algebraic convention, in which the least positive (most negative) limit is designated as minimum, is used in this data sheet.

Electrostatic Discharge Protection

PARAMETER	TEST CONDITIONS	TYP ⁽¹⁾	UNIT
Human-Body Model	Bus terminals and GND	±16	
Human-Body Model (2)	All pins	±4	kV
Charged-Device Model (3)	All pins	±1	

(1) All typical values at 25°C with 3.3-V supply

(2) Tested in accordance with JEDEC Standard 22, Test Method A114-A
 (3) Tested in accordance with JEDEC Standard 22, Test Method C101

Long-term high-temperature storage and/or extended use at maximum recommended operating conditions may result in a reduction of overall device life. See http://www.ti.com/ep_quality for additional information on enhanced plastic packaging.

SGLS367C-SEPTEMBER 2006-REVISED MARCH 2007

Driver Electrical Characteristics

	PARAMET	ER	TEST CONDITIO	NS	MIN	TYP ⁽¹⁾	MAX	UNIT
$V_{I(K)}$	Input clamp volta	ge	$I_I = -18 \text{ mA}$		-1.5			V
			I _O = 0	2.3		V _{CC} + 0.1		
V _{OD(SS)}	Steady-state diffe	erential output voltage	$R_L = 54 \Omega$, See Figure 1 (RS-	485)	1.5	2		V
(,			$R_L = 100 \Omega$, See Figure 1 (RS	5-422)	2	2.3		
			$V_{\text{test}} = -7 \text{ V to } 12 \text{ V, See Figu}$	re 2	1.5			
$\Delta V_{OD(SS)} $		tude of steady-state t voltage between	$R_L = 54 \Omega$, See Figure 1 and I	Figure 2	-0.2		0.2	V
V _{OD(RING)}	Differential outpu and undershoot	t voltage overshoot	$R_L = 54 \Omega$, $C_L = 50 pF$, See F Figure 3	igure 5 and			10%(2)	V
	Peak-to-peak	'HVD30, 'HVD33, 'HVD36, 'HVD38	See Figure 4			0.5		
V _{OC(PP)}	common-mode output voltage	'HVD31, 'HVD34, 'HVD37, 'HVD39, 'HVD32, 'HVD35				0.25		V
V _{OC(SS)}	Steady-state com voltage	nmon-mode output	See Figure 4		1.6		2.3	V
$\Delta V_{OC(SS)}$	Change in steady common-mode o		See Figure 4		-0.05		0.05	V
		'HVD30, 'HVD31,	$V_{CC} = 0 \text{ V}, V_Z \text{ or } V_Y = 12 \text{ V},$ Other input at 0 V				90	
$I_{Z(Z)}$ or	High-impedance	'HVD32, 'HVD36, 'HVD37	$V_{CC} = 0 \text{ V}, V_{Z} \text{ or } V_{Y} = -7 \text{ V},$ Other input at 0 V		-10			^
I _{Y(Z)}	state output current	'HVD33, 'HVD34, 'HVD35, 'HVD38,	V _{CC} = 3 V or 0 V, DE = 0 V, V _Z or V _Y = 12 V	Other input			90	μΑ
		'HVD39	$V_{CC} = 3 \text{ V or } 0 \text{ V, DE} = 0 \text{ V,} $ $V_{Z} \text{ or } V_{Y} = -7 \text{ V}$	at 0 V	-10			
I _{Z(S)} or	S) Or Short-circuit output current		V_Z or $V_Y = -7 V$	Other input		±250		mA
I _{Y(S)}	Short-circuit outp	ut current	V_Z or $V_Y = 12 \text{ V}$ at 0 V			±230		IIIA
I _I	Input current	D, DE			0		100	μΑ
C _(OD)	Differential outpu	t capacitance	$V_{OD} = 0.4 \sin (4E6\pi t) + 0.5 V$	DE at 0 V		16		pF

⁽¹⁾ All typical values at 25°C with 3.3-V supply

^{(2) 10%} of the peak-to-peak differential output voltage swing, per TIA/EIA-485

SN65HVD30-EP, SN65HVD31-EP, SN65HVD32-EP, SN65HVD33-EP, SN65HVD34-EP SN65HVD35-EP, SN65HVD36-EP, SN65HVD37-EP, SN65HVD38-EP, SN65HVD39-EP



SGLS367C-SEPTEMBER 2006-REVISED MARCH 2007

Driver Switching Characteristics

	PARAM	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT			
		'HVD30, 'HVD33, 'HVD36, 'HVD38		4	10	23			
t _{PLH}	Propagation delay time, low- to high-level output	'HVD31, 'HVD34, 'HVD37, 'HVD39		25	38	65	ns		
	iow to mgm lover output	'HVD32, 'HVD35		120	175	305			
		'HVD30, 'HVD33, 'HVD36, 'HVD38		4	9	23	ns		
t_{PHL}	Propagation delay time, high- to low-level output	'HVD31, 'HVD34, 'HVD37, 'HVD39		25	38	65			
	riigii to loii lovel output	'HVD32, 'HVD35		120	175	305			
		'HVD30, 'HVD33, 'HVD36, 'HVD38		2.5	5	18			
t _r	Differential output signal rise time	'HVD31, 'HVD34, 'HVD37, 'HVD39	$R_L = 54 \Omega$, $C_L = 50 pF$, See Figure 5	20	37	60	ns		
	noe une	'HVD32, 'HVD35	J Coc riguio o	120	185	300			
		'HVD30, 'HVD33, 'HVD36, 'HVD38		2.5	5	18			
t _f	Differential output signal fall time	'HVD31, 'HVD34, 'HVD37, 'HVD39		20	35	60	ns		
		'HVD32, 'HVD35		120	180	300			
		'HVD30, 'HVD33, 'HVD36, 'HVD38			0.6				
t _{sk(p)}	Pulse skew (t _{PHL} - t _{PLH})	'HVD31, 'HVD34, 'HVD37, 'HVD39			2.0		ns		
		'HVD32, 'HVD35			5.1				
	Propagation delay time,	'HVD33, 'HVD38				45	5		
t _{PZH1}	high-impedance to high-level	'HVD34, 'HVD39	D 1100 DE at 0.V			235	ns		
	output	'HVD35	R_L = 110 Ω, \overline{RE} at 0 V, D = 3 V and S1 = Y, or			490			
	Propagation delay time,	'HVD33, 'HVD38	D = 0 V and S1 = Z,			25	25 65 ns		
t_{PHZ}	high-level to high-impedance	'HVD34, 'HVD39	See Figure 6			65			
	output	'HVD35				165	165		
	Propagation delay time,	'HVD33, 'HVD38				35			
t _{PZL1}	high-impedance to low-level	'HVD34, 'HVD39	$R_1 = 110 \Omega$, \overline{RE} at 0 V,			190	ns		
	output	'HVD35	D = 3 V and S1 = Z, or			490	490 30		
	Propagation delay time,	'HVD33, 'HVD38	D = 0 V and S1 = Y,			30			
t_{PLZ}	low-level to high-impedance	'HVD34, 'HVD39	See Figure 7			120	ns		
	output	'HVD35				290			
		'HVD30	$R_L = 110 \Omega$, \overline{RE} at 3 V,			4000			
t _{PZH2}	Propagation delay time, standby to high-level output	'HVD33	D = 3 V and S1 = Y, or D = 0 V and S1 = Z, See Figure 6			5000	ns		
	'HVD30		$R_L = 110 \Omega$, \overline{RE} at 3 V,			4000			
t _{PZL2}	Propagation delay time, standby to low-level output	'HVD33	D = 3 V and S1 = Z, or D = 0 V and S1 = Y, See Figure 7			5000	ns		

⁽¹⁾ All typical values at 25°C with 3.3-V supply



Receiver Electrical Characteristics

	PARAME	TER	TEST CONDITIO	NS	MIN	TYP ⁽¹⁾	MAX	UNIT	
V _{IT+}	Positive-going differen voltage	tial input threshold	I _O = -8 mA				-0.02	V	
	Negative-going	'HVD30			-0.15				
V _{IT}	differential input threshold voltage	'HVD33	I _O = 8 mA		-0.2			V	
V _{hys}	Hysteresis voltage (V _I	r ₊ - V _{IT} -)				50		mV	
V _{IK}	Enable-input clamp vo	ltage	$I_1 = -18 \text{ mA}$		-1.5			V	
Vo	Output voltage		$V_{ID} = 200 \text{ mV}, I_{O} = -8 \text{ mA}, Se$	ee Figure 8	2.4			V	
v O	Odiput voltage		$V_{ID} = -200 \text{ mV}, I_{O} = 8 \text{ mA}, Se$	ee Figure 8			0.4	V	
$I_{O(Z)}$	High-impedance-state	output current	$V_O = 0$ or V_{CC} , \overline{RE} at V_{CC}		-1		1	μΑ	
			V_A or $V_B = 12 V$			0.05	0.1		
		'HVD31, 'HVD32, 'HVD34, 'HVD35,	V_A or $V_B = 12 V$, $V_{CC} = 0 V$	Other input		0.06	0.1		
		'HVD37, 'HVD39	V_A or $V_B = -7 V$	at 0 V	-0.10	-0.04			
_A or	Bus input current		V_A or $V_B = -7 V$, $V_{CC} = 0 V$		-0.10	-0.03		mΛ	
В	bus input current		V_A or $V_B = 12 V$		0.20 0.35	0.35	mA		
		'HVD30, 'HVD33,	V_A or $V_B = 12 \text{ V}$, $V_{CC} = 0 \text{ V}$	Other input		0.24	0.4		
		'HVD36, 'HVD38	V_A or $V_B = -7 \text{ V}$	at 0 V	-0.35	-0.18			
			V_A or $V_B = -7 V$, $V_{CC} = 0 V$		-0.25	-0.13			
I _{IH}	Input current, RE		V _{IH} = 0.8 V or 2 V		-60			μΑ	
C _{ID}	Differential input capad	citance	$V_{ID} = 0.4 \sin (4E6\pi t) + 0.5 V$,	DE at 0 V		15		pF	
Suppl	y Current								
		'HVD30					2.1		
		'HVD31, 'HVD32	D at 0 V or V _{CC} and no load				6.4	mA	
		'HVD36, 'HVD37					7.9		
		'HVD33	RE at 0 V, D at 0 V or V _{CC} , D	E at 0 V.			1.8		
		'HVD34, 'HVD35	No load (receiver enabled and				2.2		
		'HVD38, 'HVD39	disabled)				3.8		
		'HVD33, 'HVD34, 'HVD35, 'HVD38, 'HVD39	RE at V _{CC} , D at V _{CC} , DE at 0 V, No load (receiver disabled and driver disabled)			0.022	1.5	1.5 μΑ	
I_{CC}	Supply current	'HVD33					2.1		
		'HVD34, 'HVD35	RE at 0 V, D at 0 V or V _{CC} , D	E at V _{CC} ,			6.5		
		'HVD38	 No load (receiver enabled and enabled) 	a ariver			3.5		
		'HVD39					8		
		'HVD33					1.8	mA	
		'HVD34, 'HVD35 RE at V _{CC} , D at 0 V or V _{CC} , DE at V _{CC}				6.2			
		'HVD38	 No load (receiver disabled an enabled) 	a driver			2.5		
		'HVD39					7	1	

⁽¹⁾ All typical values at 25°C with 3.3-V supply

SN65HVD30-EP, SN65HVD31-EP, SN65HVD32-EP, SN65HVD33-EP, SN65HVD34-EP SN65HVD35-EP, SN65HVD36-EP, SN65HVD37-EP, SN65HVD38-EP, SN65HVD39-EP



SGLS367C-SEPTEMBER 2006-REVISED MARCH 2007

Receiver Switching Characteristics

	PARAMETER			CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT	
	Dranagation dalay time	'HVD30, 'HVD33, 'HVD36, 'HVD38			26	60			
t _{PLH}	Propagation delay time, low- to high-level output	'HVD31, 'HVD32, 'HVD34, 'HVD35, 'HVD37, 'HVD39				47	70	ns	
	Dranagation dalay time	'HVD30, 'HVD33, 'HVD36, 'HVD38				29	60		
t _{PHL}	Propagation delay time, high- to low-level output	'HVD31, 'HVD32, 'HVD34, 'HVD35, 'HVD37, 'HVD39	V ₁₀ = -1.5 V	′ to 1.5 V		49	70	ns	
t _{sk(p)}	Pulse skew (t _{PHI} - t _{PI H})	'HVD30, 'HVD33, 'HVD36, 'HVD37, 'HVD38, 'HVD39		$V_{ID} = -1.5 \text{ V to } 1.5 \text{ V},$ $C_L = 15 \text{ pF}, \text{ See Figure } 9$			12	ns	
ON(P)		'HVD31, 'HVD34, 'HVD32, 'HVD35					10		
	Output signal rise time	'HVD30					10		
t _r	Output signal rise time	'HVD33					18	ns	
t _f	Output signal fall time						12.5	ns	
t_{PHZ}	Output disable time from high	n level	DE at 3 V				20	ns	
t _{PZH1}	Output enable time to high le	evel	DE at 3 V	$C_{L} = 15 \text{ pF},$			20	ns	
	Propagation delay time,	'HVD30	DE at 0 V	See Figure 10			4000		
t _{PZH2}	standby to high-level output	'HVD33	DE al U V				5000	ns	
t _{PLZ}	Output disable time from low level		DE -+ 2 \/				20	ns	
t _{PZL1}	ZL1 Output enable time to low level		DE at 3 V	$C_{L} = 15 \text{ pF},$			20	ns	
	Propagation delay time,	'HVD30	DE at 0 V	See Figure 11			4000		
t _{PZL2}	standby to low-level output	'HVD33	DE at U V	JV			5000	ns	

⁽¹⁾ All typical values 25°C with 3.3-V supply





SGLS367C-SEPTEMBER 2006-REVISED MARCH 2007

Receiver Equalization Characteristics

over recommended operating conditions (unless otherwise noted)

ı	PARAMETER	TEST CONDIT	TIONS		DEVICE	MIN	TYP ⁽¹⁾	MAX	UNIT
				0 m	'HVD36, 'HVD38	PRE	EVIEW		
				100 m	'HVD33 ⁽²⁾	PRE	EVIEW		
				100 m	'HVD36, 'HVD38	PRE	EVIEW		
			25 Mbps	150 m	'HVD33 ⁽²⁾	PRE	EVIEW		
			130 111	'HVD36, 'HVD38	PRE	EVIEW			
			200	'HVD33 ⁽²⁾	PRE	EVIEW			
				200 m	'HVD36, 'HVD38	PRE	EVIEW		
			10 Mbps	200 m	'HVD33 ⁽²⁾	PRE	EVIEW		
		Pseudo-random NRZ code with a bit pattern length of 2 ¹⁶ – 1, Belden 3105A cable		200 111	'HVD36, 'HVD38	PRE	EVIEW		ns
	5			250 m -	'HVD33 ⁽²⁾	PRE	EVIEW		
t _{j(pp)}	Peak-to-peak eye-pattern jitter				'HVD36, 'HVD38	PRE	EVIEW		
	oyo pano j.no.				'HVD33 ⁽²⁾	PRE	EVIEW		
					'HVD36, 'HVD38	PRE	EVIEW		
			5 Mbps	500 m	'HVD34 ⁽²⁾	PRE	EVIEW		
			3 Minhs	300 111	'HVD37, 'HVD39	PRE	EVIEW		
					'HVD33 ⁽²⁾	PRE	EVIEW		
			2 Mhna	500 m	'HVD34 ⁽²⁾	PRE	EVIEW		
			3 Mbps	500 m	'HVD36, 'HVD38	PRE	EVIEW		
					'HVD37, 'HVD39	PRE	EVIEW		
			1 Mbpo	1000 m	'HVD34 ⁽²⁾	PRE	EVIEW		
			1 Mbps	1000 m	'HVD37, 'HVD39	PRE	EVIEW		

Device Power Dissipation – PD

DEVICE	TEST CONDITIONS	MIN	MAX	UNIT		
'HVD30, 'HVD36 (25 Mbps)	$R_L = 60 \Omega$, $C_L = 50 pF$, Input to D a 50% duty cycle square wave at indicated signaling rate, $T_A = 85^{\circ}C$		197			
'HVD31, 'HVD37 (5 Mbps)			213	mW		
'HVD32 (1 Mbps)	input to 2 a 50% daily typic equals that at maleated eightning rate, 14 = 55 c		193			
'HVD33, 'HVD38 (25 Mbps)	<u>-</u>		197			
'HVD34, 'HVD39 (5 Mbps)	R_L = 60 Ω , C_L = 50 pF, DE at V _{CC} , \overline{RE} at 0 V, Input to D a 50% duty cycle square wave at indicated signaling rate, T_A = 85°C				193	mW
'HVD35 (1 Mbps)			248			

 ⁽¹⁾ All typical values are at V_{CC} = 5 V and temperature = 25°C.
 (2) The SN65HVD33 and the SN65HVD34 do not have receiver equalization, but are specified for comparison.



PARAMETER MEASUREMENT INFORMATION

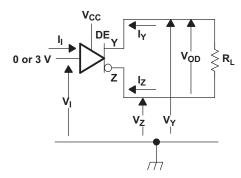


Figure 1. Driver V_{OD} Test Circuit and Voltage and Current Definitions

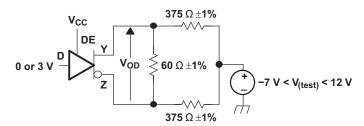


Figure 2. Driver V_{OD} With Common-Mode Loading Test Circuit

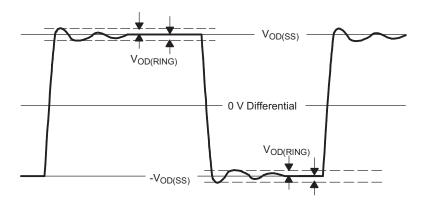
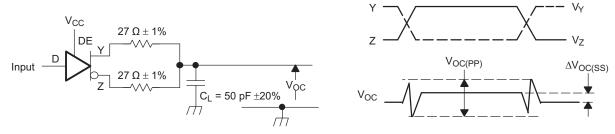


Figure 3. V_{OD(RING)} Waveform and Definitions

 $V_{\text{OD(RING)}}$ is measured at four points on the output waveform, corresponding to overshoot and undershoot from the $V_{\text{OD(H)}}$ and $V_{\text{OD(L)}}$ steady state values.

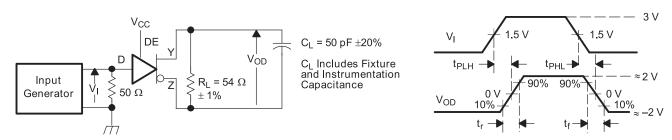


Input: PRR = 500 kHz, 50% Duty Cycle, $t_{\rm f}$ < 6 ns, $t_{\rm f}$ < 6 ns, $Z_{\rm O}$ = 50 Ω

Figure 4. Test Circuit and Definitions for Driver Common-Mode Output Voltage

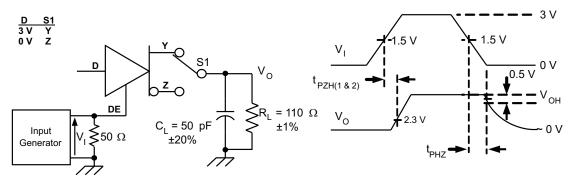


PARAMETER MEASUREMENT INFORMATION (continued)



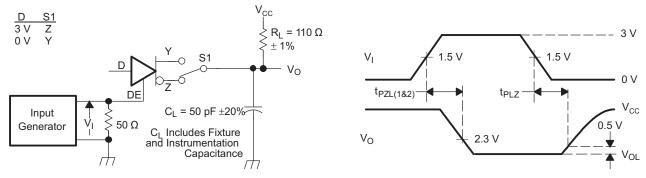
A. Generator: PRR = 500 kHz, 50% Duty Cycle, t_r < 6 ns, t_f < 6 ns, Z_O = 50 Ω

Figure 5. Driver Switching Test Circuit and Voltage Waveforms



- A. Generator: PRR = 500 kHz, 50% Duty Cycle, $t_{\rm f}$ < 6 ns, $t_{\rm f}$ < 6 ns, $Z_{\rm O}$ = 50 Ω
- B. C_I Includes Fixture and Instrumentation Capacitance

Figure 6. Driver High-Level Output Enable and Disable Time Test Circuit and Voltage Waveforms



A. Generator: PRR = 500 kHz, 50% Duty Cycle, t_r < 6 ns, t_f < 6 ns, Z_O = 50 Ω

Figure 7. Driver Low-Level Output Enable and Disable Time Test Circuit and Voltage Waveforms

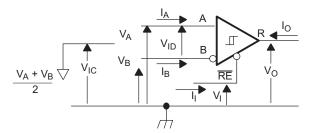
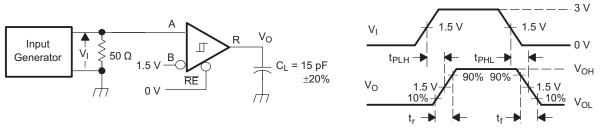


Figure 8. Receiver Voltage and Current Definitions

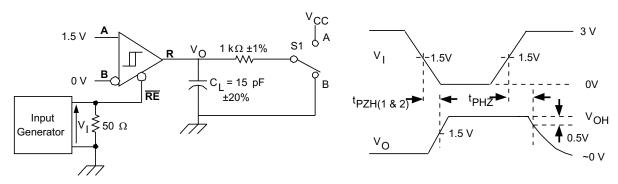


PARAMETER MEASUREMENT INFORMATION (continued)



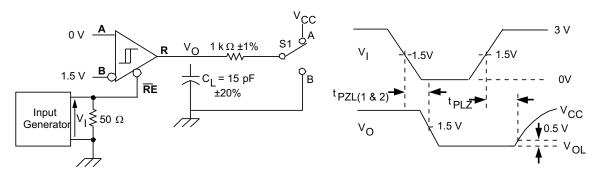
- A. C_L Includes Fixture and Instrumentation Capacitance
- B. Generator: PRR = 500 kHz, 50% Duty Cycle, t_r < 6 ns, t_f < 6 ns, Z_O = 50 Ω

Figure 9. Receiver Switching Test Circuit and Voltage Waveforms



A. Generator: PRR = 500 kHz, 50% Duty Cycle, $t_{\rm f}$ < 6 ns, $t_{\rm f}$ < 6 ns, $Z_{\rm O}$ = 50 Ω

Figure 10. Receiver High-Level Enable and Disable Time Test Circuit and Voltage Waveforms



A. Generator: PRR = 500 kHz, 50% Duty Cycle, t_r < 6 ns, t_f < 6 ns, Z_O = 50 Ω

Figure 11. Receiver Enable Time From Standby (Driver Disabled)



PARAMETER MEASUREMENT INFORMATION (continued)

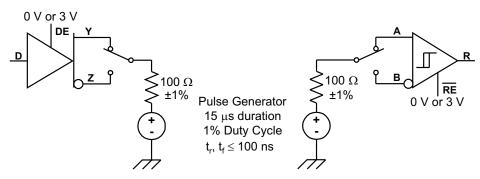


Figure 12. Test Circuit, Transient Over Voltage Test



DEVICE INFORMATION

Low-Power Standby Mode

When both the driver and receiver are disabled (DE low and RE high), the device is in standby mode. If the enable inputs are in this state for less than 60 ns, the device does not enter standby mode. This guards against inadvertently entering standby mode during driver/receiver enabling. Only when the enable inputs are held in this state for 300 ns or more, the device is assured to be in standby mode. In this low-power standby mode, most internal circuitry is powered down, and the supply current is typically less than 1 nA. When either the driver or the receiver is re-enabled, the internal circuitry becomes active.

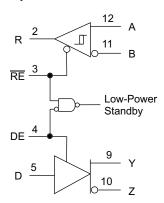


Figure 13. Low-Power Standby Logic Diagram

If only the driver is re-enabled (DE transitions to high), the driver outputs are driven according to the D input after the enable times given by t_{PZH2} and t_{PZL2} in the driver switching characteristics. If the D input is open when the driver is enabled, the driver outputs defaults to A high and B low, in accordance with the driver fail-safe feature.

If only the receiver is re-enabled (\overline{RE} transitions to low), the receiver output is driven according to the state of the bus inputs (A and B) after the enable times given by t_{PZH2} and t_{PZL2} in the receiver switching characteristics. If there is no valid state on the bus, the receiver responds as described in the fail-safe operation section.

If both the receiver and driver are re-enabled simultaneously, the receiver output is driven according to the state of the bus inputs (A and B) and the driver output is driven according to the D input. Note that the state of the active driver affects the inputs to the receiver. Therefore, the receiver outputs are valid as soon as the driver outputs are valid.



DEVICE INFORMATION (continued)

FUNCTION TABLES

SN65HVD33, SN65HVD34, SN65HVD35, SN65HVD38, SN65HVD39 DRIVER⁽¹⁾

IN	PUTS	OUTPUTS		
D	DE	Y	Z	
Н	Н	Н	L	
L	Н	L	Н	
Х	L or open	Z	Z	
Open	Н	L	Н	

(1) H = high level, L = low level, Z = high impedance, X = irrelevant

Table 1. SN65HVD33, SN65HVD34, SN65HVD35, SN65HVD38, SN65HVD39 RECEIVERSLLS6651132⁽¹⁾

DIFFERENTIAL INPUTS $V_{ID} = V_{(A)} - V_{(B)}$	ENABLE RE	OUTPUT R
$V_{ID} \le -0.2 \text{ V}$	L	L
$-0.2 \text{ V} < \text{V}_{\text{ID}} < -0.02 \text{ V}$	L	?
-0.02 V ≤ V _{ID}	L	Н
X	H or open	Z
Open circuit	L	Н
Idle circuit	L	Н
Short circuit, $V_{(A)} = V_{(B)}$	L	Н

⁽¹⁾ H = high level, L = low level, Z = high impedance, X = irrelevant,? = indeterminate

SN65HVD30, SN65HVD31, SN65HVD32, SN65HVD36, SN65HVD37 DRIVER⁽¹⁾

INPUT	OUTPUTS					
D	Y	Z				
Н	Н	L				
L	L	Н				
Open	L	Н				

⁽¹⁾ H = high level, L = low level

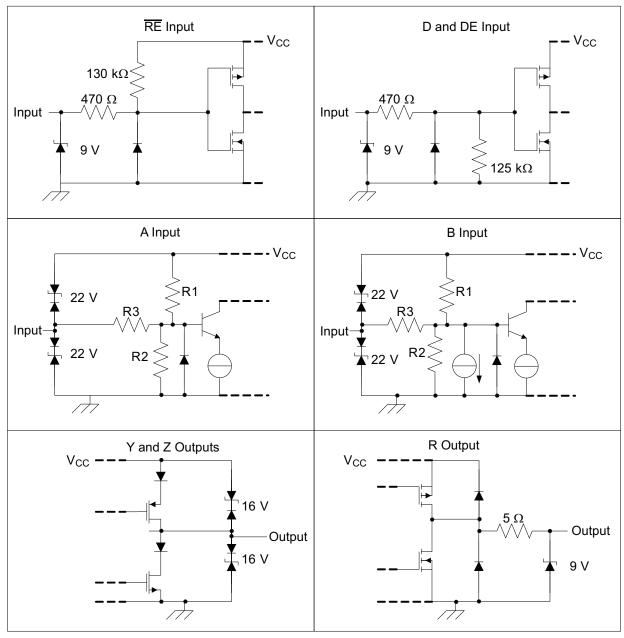
SN65HVD30, SN65HVD31, SN65HVD32, SN65HVD36, SN65HVD37 RECEIVER (1)

DIFFERENTIAL INPUTS $V_{ID} = V_{(A)} - V_{(B)}$	OUTPUT R
V _{ID} ≤ −0.15 V	L
-0.15 V < V _{ID} < -0.02 V	?
-0.02 V ≤ V _{ID}	Н
Open circuit	Н
Idle circuit	Н
Short circuit, V _(A) = V _(B)	Н

(1) H = high level, L = low level, ? = indeterminate



EQUIVALENT INPUT AND OUTPUT SCHEMATIC DIAGRAMS

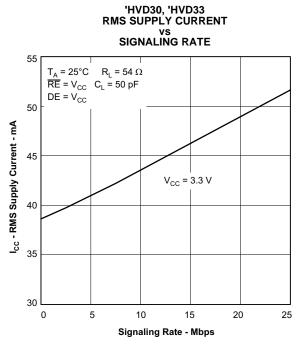


	R1/R2	R3
SN65HVD30, SN65HVD33, SN65HVD36, SN65HVD38	9 kΩ	45 kΩ
SN65HVD31, SN65HVD32, SN65HVD34, SN65HVD35 SN65HVD37, SN65HVD38, SN65HVD39	36 kΩ	180 kΩ

'HVD31, 'HVD34



TYPICAL CHARACTERISTICS



RMS SUPPLY CURRENT vs SIGNALING RATE 60 $T_A = 25^{\circ}C$ $R_L = 54 \Omega$ $\overline{RE} = V_{CC}$ $C_L = 50 pF$ DE = V_{CC} I_{CC} - RMS Supply Current - mA 50 45 V_{CC} = 3.3 V 40 35 30 0 1 3 5

Figure 14.

Signaling Rate - Mbps Figure 15.

'HVD32, 'HVD35 RMS SUPPLY CURRENT VS SIGNALING RATE

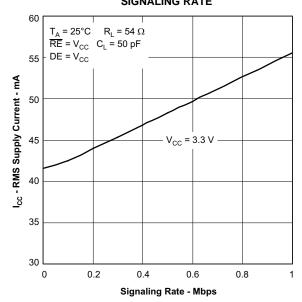


Figure 16.



TYPICAL CHARACTERISTICS (continued)

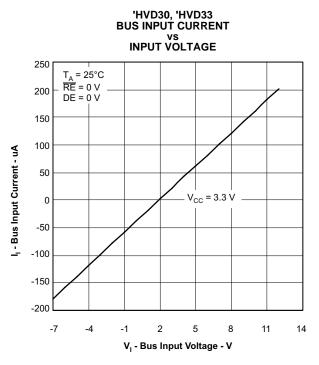


Figure 17.

DRIVER LOW-LEVEL OUTPUT CURRENT VS LOW-LEVEL OUTPUT VOLTAGE

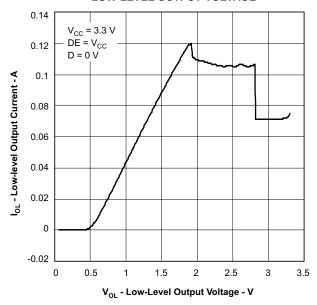


Figure 19.

'HVD31, 'HVD32, 'HVD34, 'HVD35 BUS INPUT CURRENT VS INPUT VOLTAGE

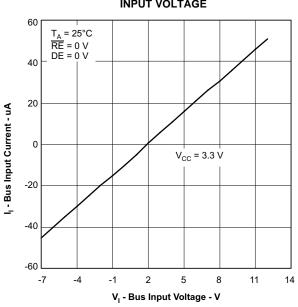


Figure 18.

DRIVER HIGH-LEVEL OUTPUT CURRENT vs HIGH-LEVEL OUTPUT VOLTAGE

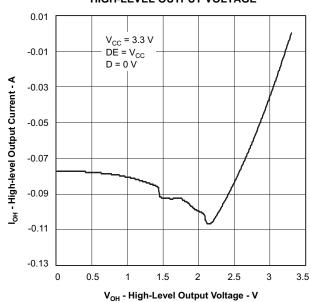


Figure 20.

18



TYPICAL CHARACTERISTICS (continued)

DRIVER DIFFERENTIAL OUTPUT VOLTAGE

vs FREE-AIR TEMPERATURE

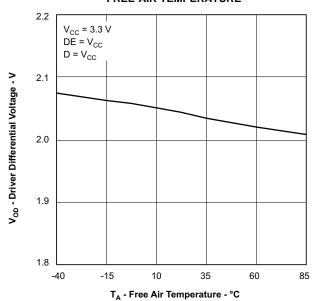


Figure 21.

DRIVER OUTPUT CURRENT VS SUPPLY VOLTAGE

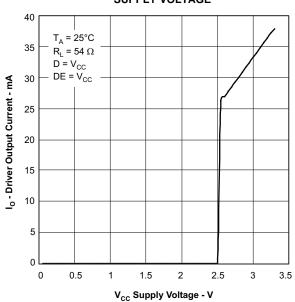


Figure 22.

PACKAGE OPTION ADDENDUM



i.com 22-Sep-2008

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
SN65HVD30MDREP	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65HVD30MDREPG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65HVD33MDREP	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65HVD33MDREPG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
V62/06634-01XE	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
V62/06634-04YE	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN65HVD30-EP, SN65HVD33-EP:

Catalog: SN65HVD30, SN65HVD33

NOTE: Qualified Version Definitions:

Catalog - TI's standard catalog product

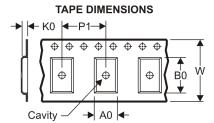




om 5-Nov-2008

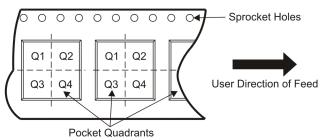
TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

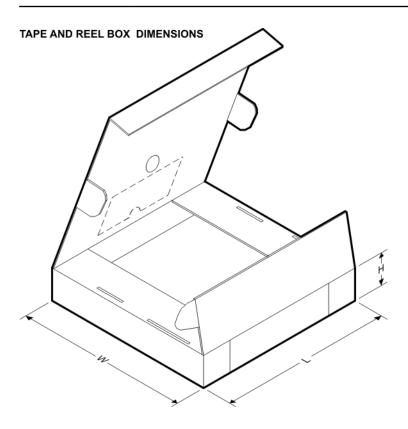


*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65HVD30MDREP	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
SN65HVD33MDREP	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1

PACKAGE MATERIALS INFORMATION

5-Nov-2008

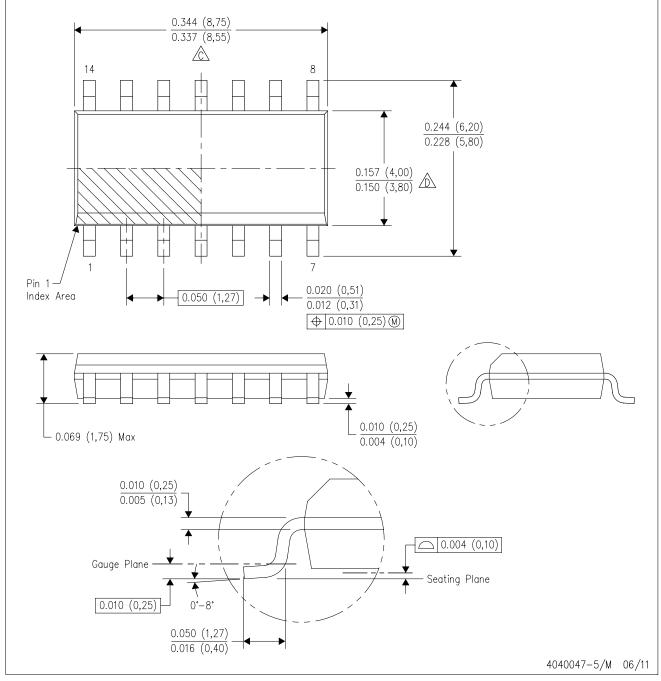


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65HVD30MDREP	SOIC	D	8	2500	346.0	346.0	29.0
SN65HVD33MDREP	SOIC	D	14	2500	333.2	345.9	28.6

D (R-PDSO-G14)

PLASTIC SMALL OUTLINE

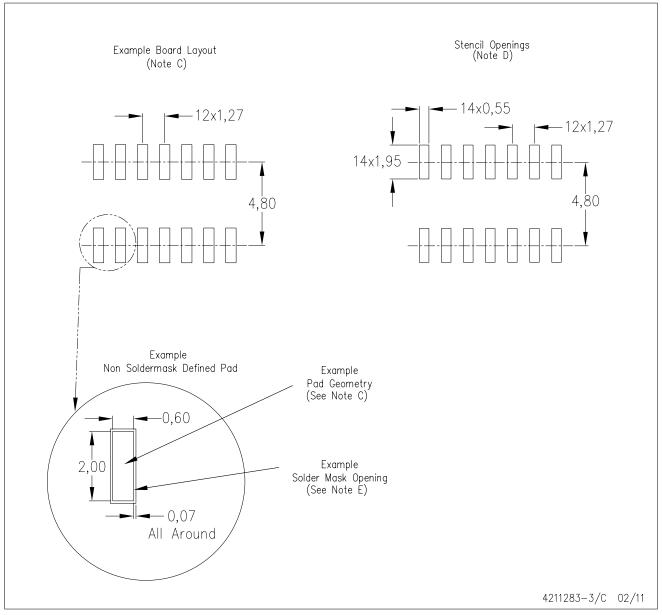


- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AB.



D (R-PDSO-G14)

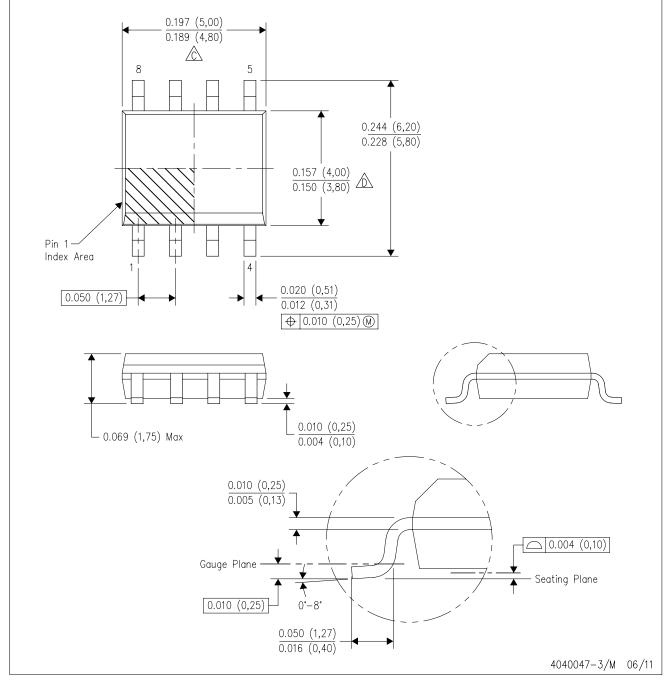
PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

D (R-PDSO-G8)

PLASTIC SMALL OUTLINE

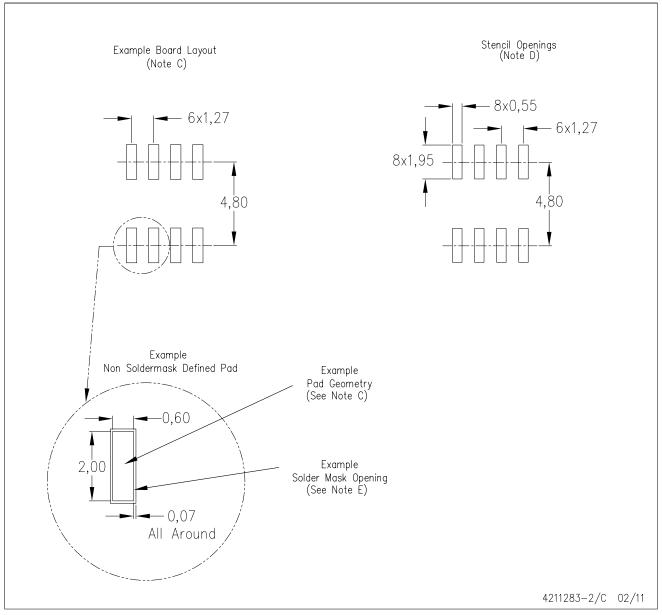


- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AA.



D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, modifications, enhancements, improvements, and other changes to its products and services at any time and to discontinue any product or service without notice. Customers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All products are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its hardware products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

TI assumes no liability for applications assistance or customer product design. Customers are responsible for their products and applications using TI components. To minimize the risks associated with customer products and applications, customers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any TI patent right, copyright, mask work right, or other TI intellectual property right relating to any combination, machine, or process in which TI products or services are used. Information published by TI regarding third-party products or services does not constitute a license from TI to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. Reproduction of this information with alteration is an unfair and deceptive business practice. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI products or services with statements different from or beyond the parameters stated by TI for that product or service voids all express and any implied warranties for the associated TI product or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

TI products are not authorized for use in safety-critical applications (such as life support) where a failure of the TI product would reasonably be expected to cause severe personal injury or death, unless officers of the parties have executed an agreement specifically governing such use. Buyers represent that they have all necessary expertise in the safety and regulatory ramifications of their applications, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of TI products in such safety-critical applications, notwithstanding any applications-related information or support that may be provided by TI. Further, Buyers must fully indemnify TI and its representatives against any damages arising out of the use of TI products in such safety-critical applications.

TI products are neither designed nor intended for use in military/aerospace applications or environments unless the TI products are specifically designated by TI as military-grade or "enhanced plastic." Only products designated by TI as military-grade meet military specifications. Buyers acknowledge and agree that any such use of TI products which TI has not designated as military-grade is solely at the Buyer's risk, and that they are solely responsible for compliance with all legal and regulatory requirements in connection with such use.

Applications

TI products are neither designed nor intended for use in automotive applications or environments unless the specific TI products are designated by TI as compliant with ISO/TS 16949 requirements. Buyers acknowledge and agree that, if they use any non-designated products in automotive applications, TI will not be responsible for any failure to meet such requirements.

Following are URLs where you can obtain information on other Texas Instruments products and application solutions:

Products

RF/IF and ZigBee® Solutions www.ti.com/lprf

Audio	www.ti.com/audio	Communications and Telecom	www.ti.com/communications
Amplifiers	amplifier.ti.com	Computers and Peripherals	www.ti.com/computers
Data Converters	dataconverter.ti.com	Consumer Electronics	www.ti.com/consumer-apps
DLP® Products	www.dlp.com	Energy and Lighting	www.ti.com/energy
DSP	dsp.ti.com	Industrial	www.ti.com/industrial
Clocks and Timers	www.ti.com/clocks	Medical	www.ti.com/medical
Interface	interface.ti.com	Security	www.ti.com/security
Logic	logic.ti.com	Space, Avionics and Defense	www.ti.com/space-avionics-defense
Power Mgmt	power.ti.com	Transportation and Automotive	www.ti.com/automotive
Microcontrollers	microcontroller.ti.com	Video and Imaging	www.ti.com/video
RFID	www.ti-rfid.com	Wireless	www.ti.com/wireless-apps

TI E2E Community Home Page <u>e2e.ti.com</u>

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2011, Texas Instruments Incorporated

